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General Purpose Transistor

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|--------------------------------------|-------------|-------------|
| Collector-Emitter Voltage | V _{CEO} | 25 | Vdc |
| Collector-Base Voltage | V _{CBO} | 25 | Vdc |
| Emitter-Base Voltage | er-Base Voltage V _{EBO} 5.0 | | Vdc |
| Collector Current – Continuous | I _C | 100 | mAdc |
| Total Device Dissipation @ T _A = 25°C Derate above 25°C | P _D | 625 5.0 | mW mW/°C |
| Total Power Dissipation @ T _A = 60°C | P _D | 450 | mW |
| Total Device Dissipation @ T _C = 25°C Derate above 25°C | P _D | 1.5 12 | W mW/°C |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -55 to +150 | °C |

THERMAL CHARACTERISTICS

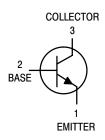
| Characteristic | Symbol | Max | Unit |
|---|-----------------|------|------|
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 200 | °C/W |
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 83.3 | °C/W |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



ON Semiconductor®

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MARKING DIAGRAM



MPS5172 = Device Code A = Assembly Location

Y = Year
WW = Work Week
Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

| Device | Package | Shipping |
|--------------|--------------------|----------------|
| MPS5172 | TO-92 | 5000 / Bulk |
| MPS5172G | TO-92 (Pb-Free) | 5000 / Bulk |
| MPS5172RLRM | TO-92 | 2000/Ammo Pack |
| MPS5172RLRMG | TO-92 (Pb-Free) | 2000/Ammo Pack |

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_{A} = 25^{\circ}C \ unless \ otherwise \ noted)$

| Characteristic | Symbol | Min | Max | Unit |
|---|----------------------|--------|-----------|--------------|
| OFF CHARACTERISTICS | <u>.</u> | | | |
| Collector-Emitter Breakdown Voltage (Note 1) (I _C = 10 mA, I _B = 0) | V _{(BR)CEO} | 25 | - | Vdc |
| Collector Cutoff Current (V _{CE} = 25 V, I _B = 0) | Ices | - | 100 | nAdc |
| Collector Cutoff Current $(V_{CB} = 25 \text{ V}, I_E = 0)$ $(V_{CB} = 25 \text{ V}, I_E = 0, T_A = 100^{\circ}\text{C})$ | I _{CBO} | - - | 100 10 | nAdc μAdc |
| Emitter Cutoff Current (V _{EB} = 5.0 V, I _C = 0) | I _{EBO} | - | 100 | nAdc |
| ON CHARACTERISTICS (Note 1) | <u>.</u> | | | |
| DC Current Gain (V _{CE} = 10 V, I _C = 10 mA) | h _{FE} | 100 | 500 | - |
| Collector-Emitter Saturation Voltage (I _C = 10 mAdc, I _B = 1.0 mAdc) | V _{CE(sat)} | - | 0.25 | Vdc |
| Base – Emitter On Voltage (I _C = 10 mAdc, V _{CE} = 10 V) | V _{BE(on)} | 0.5 | 1.25 | Vdc |
| SMALL-SIGNAL CHARACTERISTICS | | • | - | • |
| Collector–Base Capacitance (V _{CB} = 10 V, f = 1.0 MHz) | C _{cb} | 1.6 | 10 | pF |
| Small–Signal Current Gain ($I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz}$) | h _{fe} | 100 | 750 | - |

^{1.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

TYPICAL STATIC CHARACTERISTICS

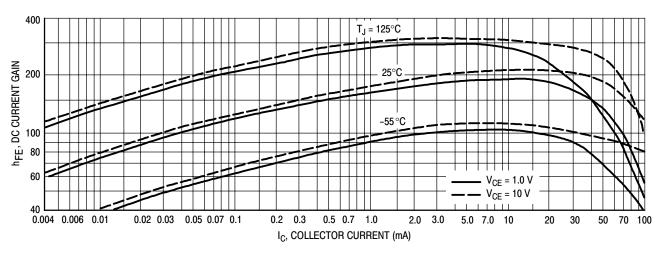


Figure 1. DC Current Gain

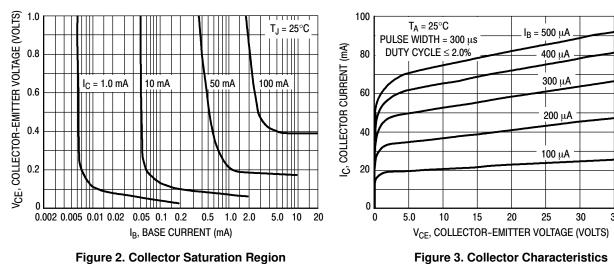


Figure 2. Collector Saturation Region

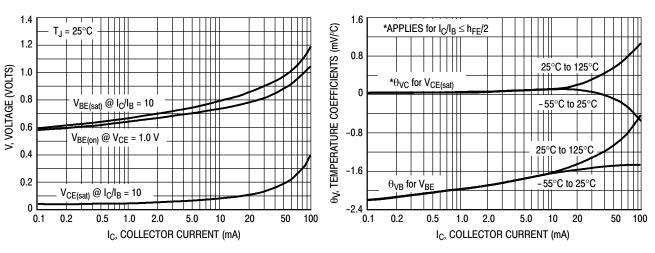
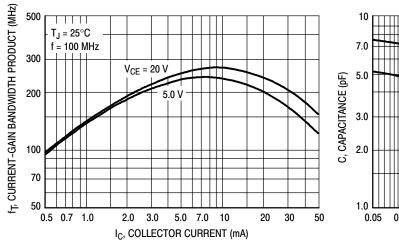


Figure 4. "On" Voltages

Figure 5. Temperature Coefficients

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TYPICAL DYNAMIC CHARACTERISTICS



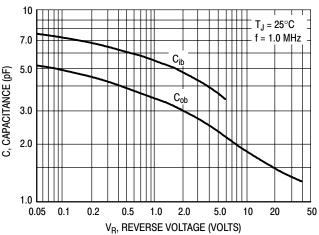


Figure 6. Current-Gain - Bandwidth Product

Figure 7. Capacitance

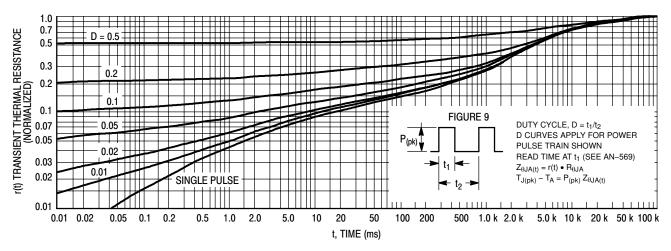


Figure 8. Thermal Response

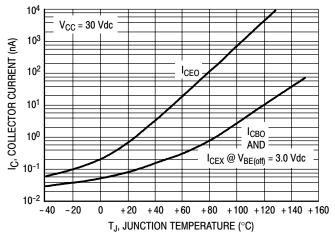


Figure 10.

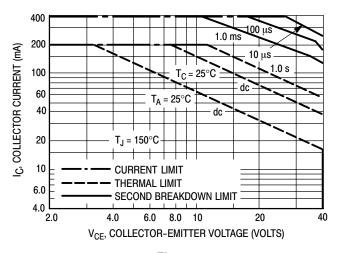


Figure 11.

DESIGN NOTE: USE OF THERMAL RESPONSE DATA

A train of periodical power pulses can be represented by the model as shown in Figure 9. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 8 was calculated for various duty cycles.

To find $Z_{\theta JA(t)}$, multiply the value obtained from Figure 8 by the steady state value $R_{\theta JA}$.

Example:

The MPS3904 is dissipating 2.0 watts peak under the following conditions:

$$t_1 = 1.0 \text{ ms}, t_2 = 5.0 \text{ ms}. (D = 0.2)$$

Using Figure 8 at a pulse width of 1.0 ms and D = 0.2, the reading of r(t) is 0.22.

The peak rise in junction temperature is therefore

$$\Delta T = r(t) \times P_{(pk)} \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88^{\circ}C.$$

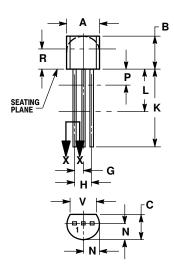
For more information, see ON Semiconductor Application Note AN569/D, available from the Literature Distribution Center or on our website at www.onsemi.com.

The safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 11 is based upon $T_{J(pk)} = 150^{\circ}C$; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 8. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

PACKAGE DIMENSIONS

TO-92 (TO-226) **CASE 29-11 ISSUE AL**





- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 114-304, 1962.
 CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R
 IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P AND 3.
- BEYOND DIMENSION K MINIMUM.

| | INCHES | | MILLIN | IETERS |
|-----|--------|-------|--------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.175 | 0.205 | 4.45 | 5.20 |
| В | 0.170 | 0.210 | 4.32 | 5.33 |
| С | 0.125 | 0.165 | 3.18 | 4.19 |
| D | 0.016 | 0.021 | 0.407 | 0.533 |
| G | 0.045 | 0.055 | 1.15 | 1.39 |
| Н | 0.095 | 0.105 | 2.42 | 2.66 |
| J | 0.015 | 0.020 | 0.39 | 0.50 |
| K | 0.500 | | 12.70 | |
| L | 0.250 | | 6.35 | |
| N | 0.080 | 0.105 | 2.04 | 2.66 |
| P | | 0.100 | | 2.54 |
| R | 0.115 | | 2.93 | |
| ٧ | 0.135 | | 3.43 | |

STYLE 1:

PIN 1. EMITTER

- 2. BASE
- COLLECTOR
- 3. SOURCE

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